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Melilite oxychalcogenide $\text{Sr}_2\text{FeGe}_2\text{OS}_6$: a phase-matching IR nonlinear optical material realized by isomorphous substitution

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3. References

1. Experimental Section

1.1 Structural Refinement

Single-crystal X-ray diffraction data (XRD) of $\text{Sr}_2\text{FeGe}_2\text{OS}_6$ were collected at 100 K using a Rigaku Oxford Hybrid Pixel Array diffractometer using Ga $K\alpha$ radiation ($\lambda = 1.3405 \text{ \AA}$). The absorption correction and crystal structure were respectively determined through multi-scan method and direct method.¹ Finally, the crystal structure was refined by full-matrix least-squares fitting on F^2 using *SHELX-2014* on Olex2.² Crystallographic information, selected bond lengths and bond angles are listed in Tables 1, S1–2 in detail. CCDC number: 2227377.

1.2 Property Characterizations

Energy dispersive X-ray spectroscopy (EDS) analysis

Semiquantitative microprobe analyses on $\text{Sr}_2\text{FeGe}_2\text{OS}_6$ were done via a field emission scanning electron microscope (JSM6700F, operating at 10 kV) equipped with an energy dispersive X-ray spectroscopy (EDS, Oxford INCA). The results showed the existence of Sr, Fe, Ge, O, and S elements in the target compound and the average molar ratios close to the chemical formulae determined by single-crystal structure solution result.

UV-vis-NIR diffuse-reflectance spectral measurements

Diffuse-reflectance spectra were performed using a PerkinElmer LAMBDA 950 spectrophotometer in the region of 200–2500 nm (BaSO_4 powder as the benchmark). The diffuse reflectance data of title compound was determined by

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the hand ground powder at room temperature and converted to absorbance automatically through the instrument via the Kubelka–Munk function.³

Thermal analysis

Thermogravimetry analysis was performed on a NETZSCH STA 449C simultaneous analyzer under flowing N₂ atmosphere. For TG, about 10 mg powder samples were placed in an Al₂O₃ crucible and heated from room temperature to 1273 K at a rate of 20 K/min.

X-ray photoelectron spectroscopy

The X-ray photoelectron spectrometer (XPS) spectra were collected by the type of ESCALAB 250Xi equipment with a monochromatized Al-K α source gun type to analyze the chemical states. The pass energy is 20 eV with the binding energy step size of 0.1 eV. Besides, using the C 1s binding energy of polluted carbon at 284.8 eV as the internal standard.

Second Harmonic Generation measurements

The SHG measurements were implemented by the Kurtz-Perry method with a 2050 nm Q-switch laser.⁴ The target material and the reference AgGaS₂ were filtered into six sections (30–46, 46–74, 74–106, 106–150, 150–210, 210–300 μ m) according to the particle size range. The frequency doubled output signals emitted from the samples were collected and recorded through the photomultiplier tube and oscilloscope, respectively.

Laser-induced damage threshold measurements

The LIDT of Sr₂FeGe₂OS₆ at the particle size range of 150–210 μ m was tested by

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single pulse measurement method⁵ using a 1064 nm laser beam ($\tau_p = 10$ ns). With the increasing of the pulse energy, the apparent change of samples and the power of laser beam were respectively monitored by an optical microscope and a Nova II sensor with a PE50-DIF-C energy sensor. Besides, the damage spot radii were measured by a Vernier caliper.

2. Computational Details

The DFT calculations have been performed using the *Vienna ab initio simulation package* (VASP)⁶⁻⁸ with the Perdew-Burke-Ernzerhof (PBE)⁹ exchange correlation functional. The projected augmented wave (PAW)¹⁰ potentials have been used. A Γ -centered $5 \times 5 \times 7$ Monkhorst-Pack grid for the Brillouin zone sampling¹¹ and a cutoff energy of 750 eV for the plane wave expansion were found to get convergent lattice parameters. The linear and nonlinear optical calculation was performed in the condition of a Monkhorst-Pack k -point mesh of $5 \times 5 \times 5$.

The imaginary part of the dielectric function due to direct inter-band transitions is given by the expression:

$$\varepsilon_2(\hbar\omega) = \frac{2e^2\pi}{\Omega\varepsilon_0} \sum_{k,v,c} \left| \langle \psi_k^c | \mathbf{u} \cdot \mathbf{r} | \psi_k^v \rangle \right|^2 \delta(E_k^c - E_k^v - E) \quad \dots\dots\dots (1)$$

where Ω , ω , u , v and c are the unit-cell volume, photon frequencies, the vector defining the polarization of the incident electric field, valence and conduction bands, respectively. The real part of the dielectric function is obtained from ε_2 by a Kramers-Kronig transformation:

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$$\varepsilon_1(\omega) = 1 + \left(\frac{2}{\pi}\right) \int_0^{+\infty} d\omega' \frac{\omega'^2 \varepsilon_2(\omega')}{\omega'^2 - \omega^2} \dots\dots\dots (2)$$

The refractive index $n(\omega)$ can be obtained based on ε_1 and ε_2 .

In calculation of the static $\chi^{(2)}$ coefficients, the so-called length-gauge formalism¹² derived by Aversa and Sipe¹³ and modified by Rashkeev et al¹⁴ is adopted, which has proven to be successful in calculating the second order susceptibility for semiconductors and insulators. In the static case, the imaginary part of the static second-order optical susceptibility can be expressed as:

$$\begin{aligned} & \chi^{abc} \\ &= \frac{e^3}{\hbar^2 \Omega} \sum_{nml,k} \frac{r_{nm}^a (r_{ml}^b r_{ln}^c + r_{ml}^c r_{ln}^b)}{2\omega_{nm} \omega_{ml} \omega_{ln}} [\omega_n f_{ml} + \omega_m f_{ln} + \omega_l f_{nm}] \\ &+ \frac{ie^3}{4\hbar^2 \Omega} \sum_{nm,k} \frac{f_{nm}}{\omega_{mn}^2} [r_{nm}^a (r_{mn;c}^b + r_{mn;b}^c) + r_{nm}^b (r_{mn;c}^a + r_{mn;a}^c) + r_{nm}^c (r_{mn;b}^a + r_{mn;a}^b)] \\ &\dots\dots\dots(3) \end{aligned}$$

where r is the position operator, $\hbar\omega_{nm} = \hbar\omega_n - \hbar\omega_m$ is the energy difference for the bands m and n , $f_{mn} = f_m - f_n$ is the difference of the Fermi distribution functions, subscripts a , b , and c are Cartesian indices, and $r_{mn;a}^b$ is the so-called generalized derivative of the coordinate operator in k space,

$$r_{nm;a}^b = \frac{r_{nm}^a \Delta_{mn}^b + r_{nm}^b \Delta_{mn}^a}{\omega_{nm}} + \frac{i}{\omega_{nm}} \times \sum_l (\omega_{lm} r_{nl}^a r_{lm}^b - \omega_{nl} r_{nl}^b r_{lm}^a) \dots\dots\dots (4)$$

where $\Delta_{nm}^a = (p_{nn}^a - p_{mm}^a) / m$ is the difference between the electronic velocities at the bands n and m .

As the nonlinear optical coefficients is sensitive to the momentum matrix, much finer k-point grid and large amount of empty bands are required to obtain a convergent $\chi^{(2)}$ coefficient. The $\chi^{(2)}$ coefficients here were calculated from PBE wave

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functions and a scissor operator has been added to correct the conduction band energy (corrected to the experimental gap), which has proven to be reliable in predicting the second order susceptibility for semiconductors and insulators.

The value of the polycrystalline effective SHG coefficient d_{eff} was determined with the angular average effective NLO coefficient square $\langle d_{eff}^2 \rangle$:

$$\langle d_{eff}^2 \rangle = \frac{19}{105} \sum_i d_{iii}^2 + \frac{13}{105} \sum_{i \neq j} d_{iii} d_{ijj} + \frac{44}{105} \sum_{i \neq j} d_{ijj}^2 + \frac{13}{105} \sum_{ijk, cycle} d_{ijj} d_{jkk} + \frac{5}{7} d_{ijk}^2$$

2. Figures and Tables

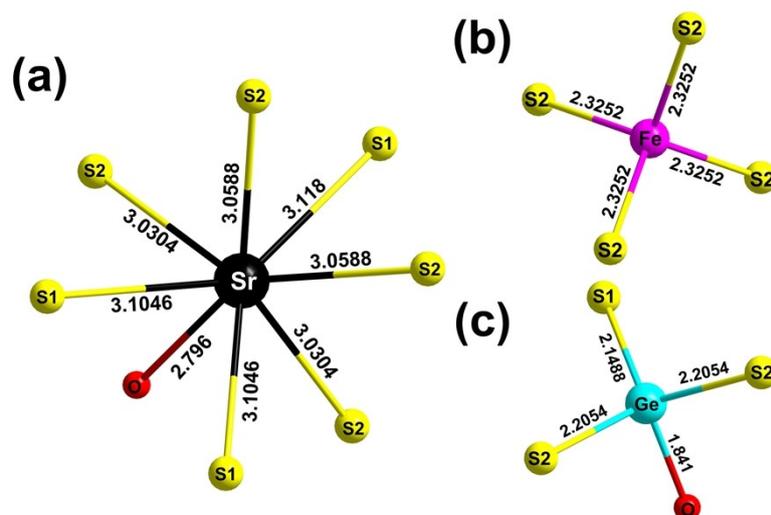


Figure S1. Coordination geometry of the Sr, Fe, and Ge atoms.

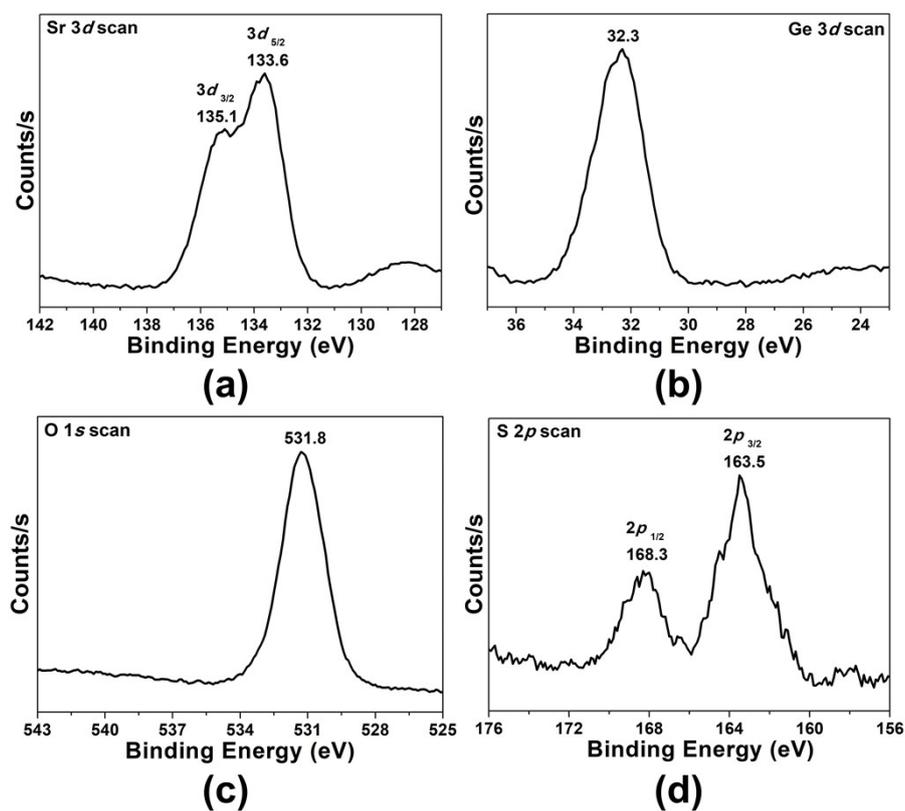


Figure S2. XPS spectra of $\text{Sr}_2\text{FeGe}_2\text{OS}_6$. (a) Sr-3d; (b) Ge-3d; (c) O-1s; (d) S-2p.

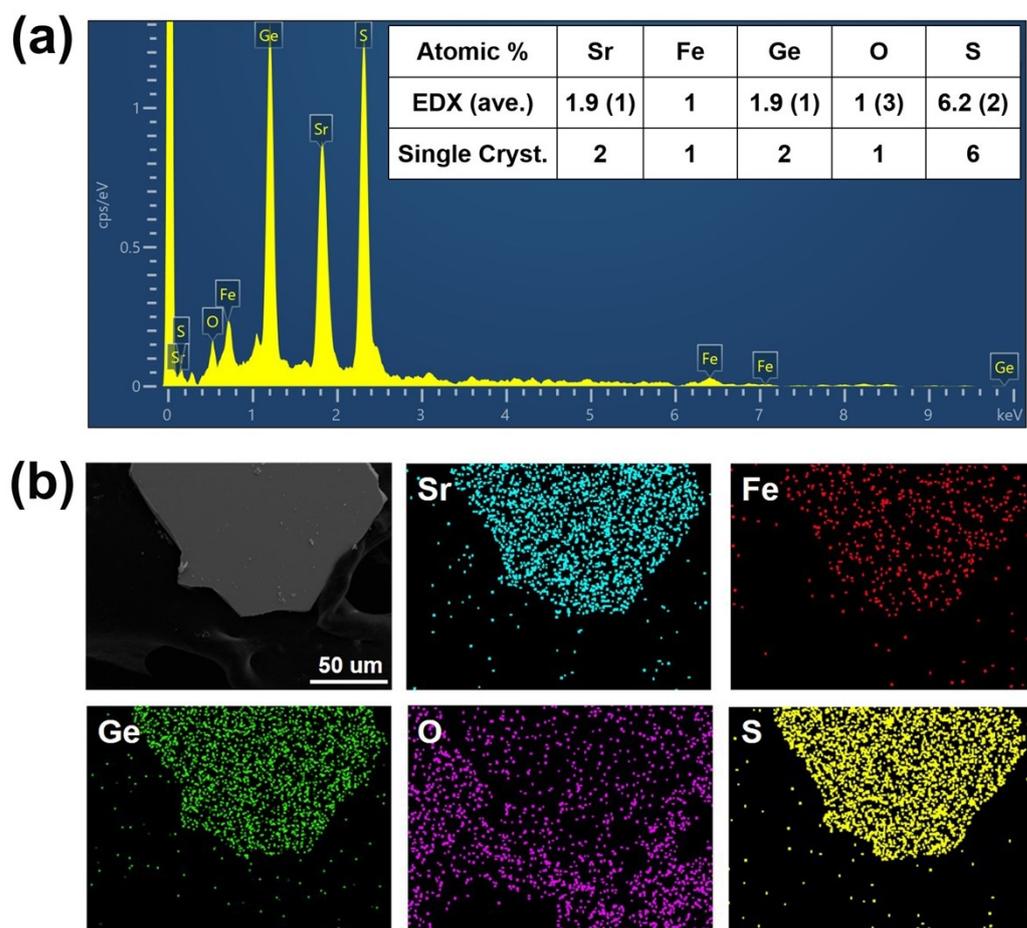


Figure S3. (a) EDX results; (b) SEM image and the corresponding elemental mapping analysis.

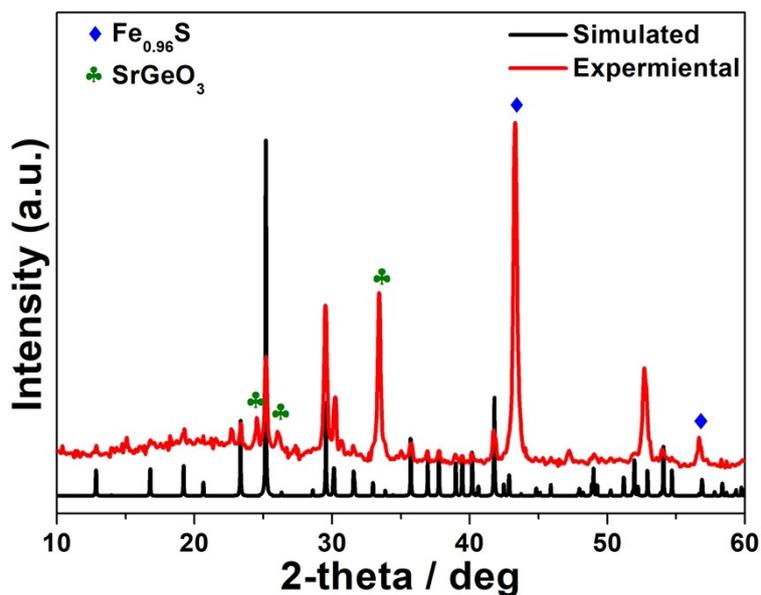


Figure S4. Powder XRD patterns of heated at 1223 K (red) and the simulated one (black).

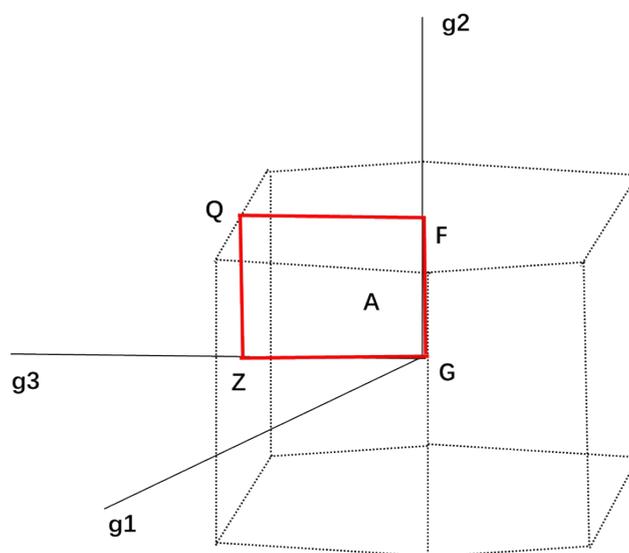


Figure S5. The first Brillouin zone with high symmetry points (red) of Sr₂FeGe₂OS₆.

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Table S1. Atomic coordinates and equivalent isotropic displacement parameters of Sr₂FeGe₂OS₆.

Atom	Wyckoff	<i>x</i>	<i>y</i>	<i>z</i>	<i>U</i> _{eq} (Å) ^a
Sr	4 <i>e</i>	0.15796(4)	0.65796(4)	0.50129(10)	0.00387(19)
Fe	2 <i>a</i>	0	0	0	0.0033(3)
Ge	4 <i>e</i>	0.62657(6)	0.12657(6)	0.91859(12)	0.0024(2)
S1	4 <i>e</i>	0.63423(12)	0.13423(12)	0.2678(3)	0.0040(3)
S2	8 <i>f</i>	0.06231(12)	0.17604(12)	0.24742(18)	0.0038(3)
O	2 <i>c</i>	0	0.5	0.2018(10)	0.0039(14)

*U*_{eq} is defined as one third of the trace of the orthogonalized *U*_{ij} tensor.

Table S2. Selected bond lengths (Å) and angles (°) of Sr₂FeGe₂OS₆.

Sr–O	2.796(4)	∠S2–Fe–S2×4	115.33(3)
Sr–S2×2	3.0304(12)	∠S2–Fe–S2×2	98.30(5)
Sr–S2×2	3.0588(12)	∠O–Ge–S1	116.42(18)
Sr–S1×2	3.1046(12)	∠O–Ge–S2×2	100.50(11)
Sr–S1	3.1180(17)	∠S1–Ge–S2×2	116.30(4)
Fe–S2×4	2.3252(11)	∠S2–Ge–S2	104.39(7)
Ge–O	1.841(3)		
Ge–S1	2.1488(17)		
Ge–S2×2	2.2054(11)		

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Table S3. Summary of the NLO properties and M–S bond length of Sr₂FeGe₂OS₆ and the reported melilite oxychalcogenides AE₂MM'OS₆ (M and M' represent a variety of metal elements from divalent to tetravalent states).

*N/A = not available.

Compound	E_g (eV)	d_{eff} (×AGS)	LIDT (×AGS)	Δn	M–S (Å)	Ref.
	3.73	0.6	20.6	0.114@2050 nm	2.3368	15
Sr ₂ ZnGe ₂ OS ₆	3.30	0.6	N/A	0.124@2000 nm	2.327	16
	3.0	0.3	13.7	0.123@1064 nm	2.3247	17
	3.62	0.8	19.2	0.193@2050 nm	2.4848	15
Sr ₂ CdGe ₂ OS ₆	3.13	0.7	N/A	0.141@2000 nm	2.493	16
	2.95	1.3	5.6	0.143@1064 nm	2.4929	17
Sr ₂ ZnSn ₂ OS ₆	3.52	0.7	10.0	0.14@2090 nm	2.3328	18
Sr ₂ MnGe ₂ OS ₆	3.51	0.3	17.4	0.064@2050 nm	2.3994	15
Ca ₂ GeGa ₂ OS ₆	3.15	2.1	9.7	0.135@1064 nm	–	17
Sr ₂ GeGa ₂ OS ₆	3.15	1.7	12.4	0.106@1064 nm	–	17
Sr ₂ CoGe ₂ OS ₆	2.77	0.34	2.13	0.09@2100 nm	2.3064	19
Sr₂FeGe₂OS₆	2.24	0.5	5.2	0.127@2050 nm	2.3252	This work

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